



R-C Thermal Model Parameters

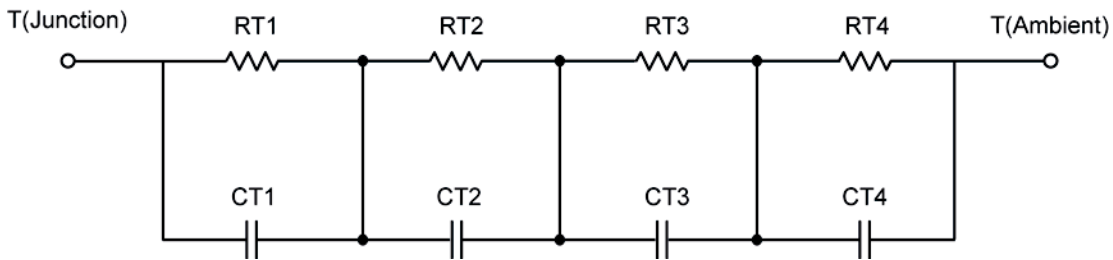
DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

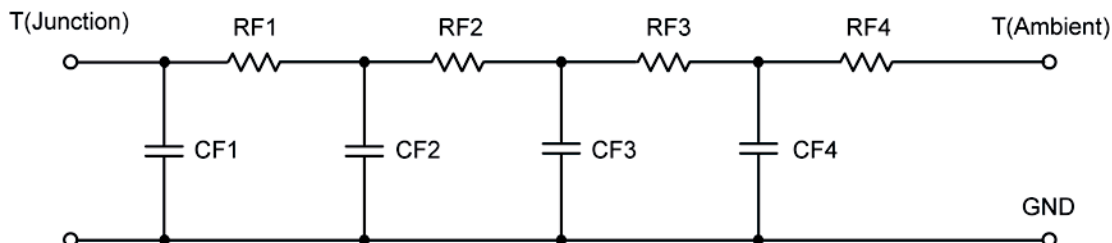
Note:
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION					
Thermal Resistance (°C/W)					
Junction to	Ambient Nch	Ambient Pch	Case	Foot Nch	Foot Pch
RT1	48.0374	48.0374	N/A	32.0266	32.0266
RT2	8.6873	8.6873	N/A	19.4793	19.4793
RT3	45.0184	45.0184	N/A	24.9093	24.9093
RT4	48.2569	48.2569	N/A	3.5122	3.5122
Thermal Capacitance (Joules/°C)					
Junction to	Ambient Nch	Ambient Pch	Case	Foot Nch	Foot Pch
CT1	27.4375 m	27.4375 m	N/A	36.5693 m	36.5693 m
CT2	2.1458 m	2.1458 m	N/A	4.7455 m	4.7455 m
CT3	6.5026 m	6.5026 m	N/A	14.7293 m	14.7293 m
CT4	1.4630	1.4630	N/A	627.8455 u	627.8455 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)					
Junction to	Ambient Nch	Ambient Pch	Case	Foot Nch	Foot Pch
RF1	29.4283	29.4283	N/A	4.5385	4.5385
RF2	57.9672	57.9672	N/A	21.8045	21.8045
RF3	14.9632	14.9632	N/A	33.2166	33.2166
RF4	47.6413	47.6413	N/A	20.4404	20.4404
Thermal Capacitance (Joules/°C)					
Junction to	Ambient Nch	Ambient Pch	Case	Foot Nch	Foot Pch
CF1	1.8196 m	1.8196 m	N/A	394.4165 u	394.4165 u
CF2	9.1194 m	9.1194 m	N/A	2.6911 m	2.6911 m
CF3	1.9156 m	1.9156 m	N/A	3.7818 m	3.7818 m
CF4	1.4004	1.4004	N/A	49.0134 m	49.0134 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

